



# 128Kx8 MONOLITHIC FLASH, SMD 5962-96690

## FEATURES

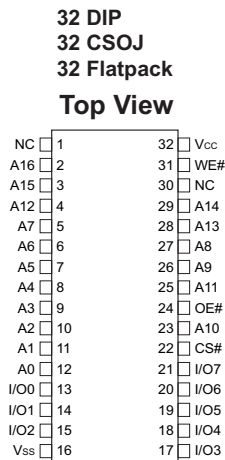
- Access Times of 50\*, 60, 70, 90, 120, 150ns
- Packaging
  - 32 lead, Hermetic Ceramic, 0.400" SOJ (Package 101)
  - 32 pin, Hermetic Ceramic, 0.600" DIP (Package 300)
  - 32 lead, Flatpack (Package 220)
  - 32 lead, Formed Flatpack (Package 221)
  - 32 pin, Rectangular Ceramic Leadless Chip Carrier (Package 601)
- 100,000 Erase/Program Cycles Minimum
- Sector Erase Architecture
  - 8 equal size sectors of 16KBytes each
  - Any combination of sectors can be concurrently erased. Also supports full chip erase
- Organized as 128Kx8
- Commercial, Industrial and Military Temperature Ranges
- 5 Volt Programming. 5V ± 10% Supply.
- Low Power CMOS
- Embedded Erase and Program Algorithms
- TTL Compatible Inputs and CMOS Outputs
- Page Program Operation and Internal Program Control Time.

This product is subject to change without notice.

Note: For programming information refer to Flash Programming 1M5 Application Note.

\* The access time of 50ns is available in Industrial and Commercial temperature ranges only.

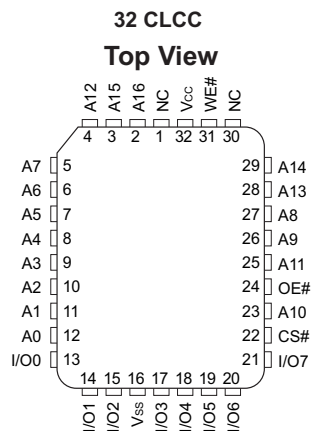
### Pin Configuration For WMF128K8-XXX5



### Pin Description

A0-16	Address Inputs
I/O0-7	Data Input/Output
CS#	Chip Select
OE#	Output Enable
WE#	Write Enable
V <sub>cc</sub>	+5.0V Power
V <sub>ss</sub>	Ground

### Pin Configuration For WMF128K8-XCLX5





**ABSOLUTE MAXIMUM RATINGS (1)**

Parameter		Unit
Operating Temperature	-55 to +125	°C
Supply Voltage (V <sub>CC</sub> )	-2.0 to +7.0	V
Signal Voltage Range (any pin except A9) (2)	-2.0 to +7.0	V
Storage Temperature Range	-65 to +150	°C
Lead Temperature (soldering, 10 seconds)	+300	°C
Data Retention Mil Temp	10	years
Endurance (write/erase cycles) (Mil Temp)	10,000 min	cycles
A9 Voltage for sector protect (V <sub>ID</sub> ) (3)	-2.0 to +14.0	V

**RECOMMENDED OPERATING CONDITIONS**

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V <sub>CC</sub>	4.5	5.5	V
Input High Voltage	V <sub>IH</sub>	2.0	V <sub>CC</sub> + 0.5	V
Input Low Voltage	V <sub>IL</sub>	-0.5	+0.8	V
Operating Temp. (Mil.)	T <sub>A</sub>	-55	+125	°C
Operating Temp. (Ind.)	T <sub>A</sub>	-40	+85	°C
A9 Voltage for Sector Protect	V <sub>ID</sub>	11.5	12.5	V

**CAPACITANCE**

T<sub>A</sub> = +25°C

Parameter	Symbol	Conditions	Max	Unit
Address Input capacitance	C <sub>AD</sub>	V <sub>I/O</sub> = 0 V, f = 1.0 MHz	15	pF
Output Enable capacitance	C <sub>OE</sub>	V <sub>IN</sub> = 0 V, f = 1.0 MHz	15	pF
Write Enable capacitance	C <sub>WE</sub>	V <sub>IN</sub> = 0 V, f = 1.0 MHz	15	pF
Chip Select capacitance	C <sub>CS</sub>	V <sub>IN</sub> = 0 V, f = 1.0 MHz	15	pF
Data I/O capacitance	C <sub>I/O</sub>	V <sub>I/O</sub> = 0 V, f = 1.0 MHz	15	pF

This parameter is guaranteed by design but not tested.

NOTES:

- Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.
- Minimum DC voltage on input or I/O pins is -0.5V. During voltage transitions, inputs may overshoot V<sub>SS</sub> to -2.0 V for periods of up to 20ns. Maximum DC voltage on output and I/O pins is V<sub>CC</sub> + 0.5V. During voltage transitions, outputs may overshoot to V<sub>CC</sub> + 2.0 V for periods of up to 20ns.
- Minimum DC input voltage on A9 pin is -0.5V. During voltage transitions, A9 may overshoot V<sub>SS</sub> to -2V for periods of up to 20ns. Maximum DC input voltage on A9 is +13.5V which may overshoot to 14.0 V for periods up to 20ns.

**DC CHARACTERISTICS — CMOS COMPATIBLE**

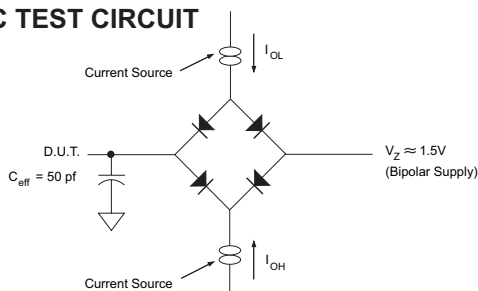
V<sub>CC</sub> = 5.0V, V<sub>SS</sub> = 0V, -55°C ≤ T<sub>A</sub> ≤ +125°C

Parameter	Symbol	Conditions	Min	Max	Unit
Input Leakage Current	I <sub>LI</sub>	V <sub>CC</sub> = 5.5, V <sub>IN</sub> = GND to V <sub>CC</sub>		10	µA
Output Leakage Current	I <sub>LO</sub>	V <sub>CC</sub> = 5.5, V <sub>IN</sub> = GND to V <sub>CC</sub>		10	µA
V <sub>CC</sub> Active Current for Read (1)	I <sub>CC1</sub>	CS# = V <sub>IL</sub> , OE# = V <sub>IH</sub>		35	mA
V <sub>CC</sub> Active Current for Program or Erase (2)	I <sub>CC2</sub>	CS# = V <sub>IL</sub> , OE# = V <sub>IH</sub>		50	mA
V <sub>CC</sub> Standby Current	I <sub>CC3</sub>	V <sub>CC</sub> = 5.5, CS# = V <sub>IH</sub> , f = 5MHz		1.6	mA
Output Low Voltage	V <sub>OL</sub>	I <sub>OL</sub> = 8.0 mA, V <sub>CC</sub> = 4.5		0.45	V
Output High Voltage	V <sub>OH1</sub>	I <sub>OH</sub> = -2.5 mA, V <sub>CC</sub> = 4.5	0.85 x V <sub>CC</sub>		V
Output High Voltage	V <sub>OH2</sub>	I <sub>OH</sub> = -100 µA, V <sub>CC</sub> = 4.5	V <sub>CC</sub> - 0.4		V
Low V <sub>CC</sub> Lock-Out Voltage	V <sub>LKO</sub>		3.2		V

NOTES:

- The I<sub>CC</sub> current listed includes both the DC operating current and the frequency dependent component (at 5 MHz). The frequency component typically is less than 2 mA/MHz, with OE# at V<sub>IH</sub>.
- I<sub>CC</sub> active while Embedded Algorithm (program or erase) is in progress.
- DC test conditions: V<sub>IL</sub> = 0.3V, V<sub>IH</sub> = V<sub>CC</sub> - 0.3V

**AC TEST CIRCUIT**



**AC TEST CONDITIONS**

Parameter	Typ	Unit
Input Pulse Levels	V <sub>IL</sub> = 0, V <sub>IH</sub> = 3.0	V
Input Rise and Fall	5	ns
Input and Output Reference Level	1.5	V
Output Timing Reference Level	1.5	V

Notes:  
 V<sub>Z</sub> is programmable from -2V to +7V.  
 I<sub>OL</sub> & I<sub>OH</sub> programmable from 0 to 16mA.  
 Tester Impedance Z<sub>0</sub> = 75 Ω.  
 V<sub>Z</sub> is typically the midpoint of V<sub>OH</sub> and V<sub>OL</sub>.  
 I<sub>OL</sub> & I<sub>OH</sub> are adjusted to simulate a typical resistive load circuit.  
 ATE tester includes jig capacitance.



**AC CHARACTERISTICS – WRITE/ERASE/PROGRAM OPERATIONS, WE# CONTROLLED**

V<sub>CC</sub> = 5.0V, V<sub>SS</sub> = 0V, -55°C ≤ T<sub>A</sub> ≤ +125°C

Parameter	Symbol		-50		-60		-70		-90		-120		-150		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	t <sub>AVAV</sub>	t <sub>WC</sub>	50		60		70		90		120		150		ns
Chip Select Setup Time	t <sub>ELWL</sub>	t <sub>CS</sub>	0		0		0		0		0		0		ns
Write Enable Pulse Width	t <sub>WLWH</sub>	t <sub>WP</sub>	25		30		35		45		50		50		ns
Address Setup Time	t <sub>AVWH</sub>	t <sub>AS</sub>	0		0		0		0		0		0		ns
Data Setup Time	t <sub>DVWH</sub>	t <sub>DS</sub>	25		30		30		45		50		50		ns
Data Hold Time	t <sub>WHDX</sub>	t <sub>DH</sub>	0		0		0		0		0		0		ns
Address Hold Time	t <sub>WHAX</sub>	t <sub>AH</sub>	40		45		45		45		50		50		ns
Chip Select Hold Time	t <sub>WHEH</sub>	t <sub>CH</sub>	0		0		0		0		0		0		ns
Write Enable Pulse Width High	t <sub>WHWL</sub>	t <sub>WPH</sub>	20		20		20		20		20		20		ns
Duration of Byte Programming Operation (min)	t <sub>WHWH1</sub>		14		14		14		14		14		14		µs
Sector Erase Time	t <sub>WHWH2</sub>		2.2	60	2.2	60	2.2	60	2.2	60	2.2	60	2.2	60	sec
Read Recovery Time before Write	t <sub>GHWL</sub>		0		0		0		0		0		0		ms
V <sub>CC</sub> Set-up Time		t <sub>VCS</sub>	50		50		50		50		50		50		µs
Chip Programming Time				12.5		12.5		12.5		12.5		12.5		12.5	sec
Output Enable Setup Time		t <sub>OES</sub>	0		0		0		0		0		0		ns
Output Enable Hold Time (1)		t <sub>OEH</sub>	10		10		10		10		10		10		ns

NOTES:

1. For Toggle and Data# Polling.

**AC CHARACTERISTICS – READ ONLY OPERATIONS**

V<sub>CC</sub> = 5.0V, V<sub>SS</sub> = 0V, -55°C ≤ T<sub>A</sub> ≤ +125°C

Parameter	Symbol		-50		-60		-70		-90		-120		-150		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Read Cycle Time	t <sub>AVAV</sub>	t <sub>RC</sub>	50		60		70		90		120		150		ns
Address Access Time	t <sub>AVQV</sub>	t <sub>ACC</sub>		50		60		70		90		120		150	ns
Chip Select Access Time	t <sub>ELQV</sub>	t <sub>CE</sub>		50		60		70		90		120		150	ns
OE# to Output Valid	t <sub>GLQV</sub>	t <sub>OE</sub>		25		30		35		40		50		55	ns
Chip Select to Output High Z (1)	t <sub>EHQZ</sub>	t <sub>DF</sub>		20		20		20		25		30		35	ns
OE# High to Output High Z (1)	t <sub>GHQZ</sub>	t <sub>DF</sub>		20		20		20		25		30		35	ns
Output Hold from Address, CS# or OE# Change, whichever is First	t <sub>AXQX</sub>	t <sub>OH</sub>	0		0		0		0		0		0		ns

NOTES:

1. Guaranteed by design, but not tested



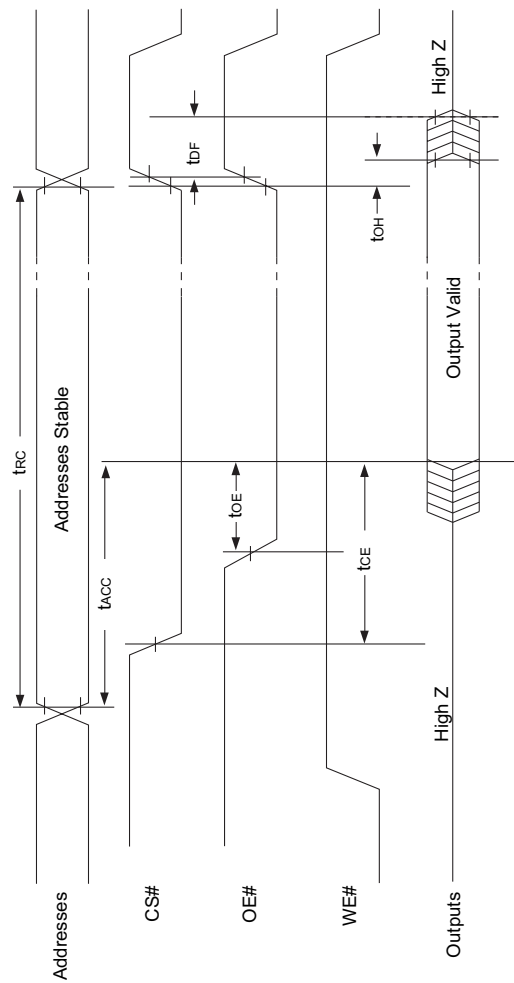
**AC CHARACTERISTICS – WRITE/ERASE/PROGRAM OPERATIONS, CS# CONTROLLED**

V<sub>CC</sub> = 5.0V, V<sub>SS</sub> = 0V, -55°C ≤ T<sub>A</sub> ≤ +125°C

Parameter	Symbol		-50		-60		-70		-90		-120		-150		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	t <sub>AVAV</sub>	t <sub>WC</sub>	50		60		70		90		120		150		ns
WE# Setup Time	t <sub>WLEL</sub>	t <sub>WS</sub>	0		0		0		0		0		0		ns
CS# Pulse Width	t <sub>ELEH</sub>	t <sub>CP</sub>	25		30		35		45		50		50		ns
Address Setup Time	t <sub>AVEL</sub>	t <sub>AS</sub>	0		0		0		0		0		0		ns
Data Setup Time	t <sub>DVEH</sub>	t <sub>DS</sub>	25		30		30		45		50		50		ns
Data Hold Time	t <sub>EHDX</sub>	t <sub>DH</sub>	0		0		0		0		0		0		ns
Address Hold Time	t <sub>ELAX</sub>	t <sub>AH</sub>	40		45		45		45		50		50		ns
WE# Hold from WE# High	t <sub>EHWH</sub>	t <sub>WH</sub>	0		0		0		0		0		0		ns
CS# Pulse Width High	t <sub>EHEL</sub>	t <sub>CPH</sub>	20		20		20		20		20		20		ns
Duration of Programming Operation	t <sub>WHWH1</sub>		14		14		14		14		14		14		µs
Duration of Erase Operation	t <sub>WHWH2</sub>		2.2	60	2.2	60	2.2	60	2.2	60	2.2	60	2.2	60	sec
Read Recovery before Write	t <sub>GHEL</sub>		0		0		0		0		0		0		ns
Chip Programming Time				12.5		12.5		12.5		12.5		12.5		12.5	sec

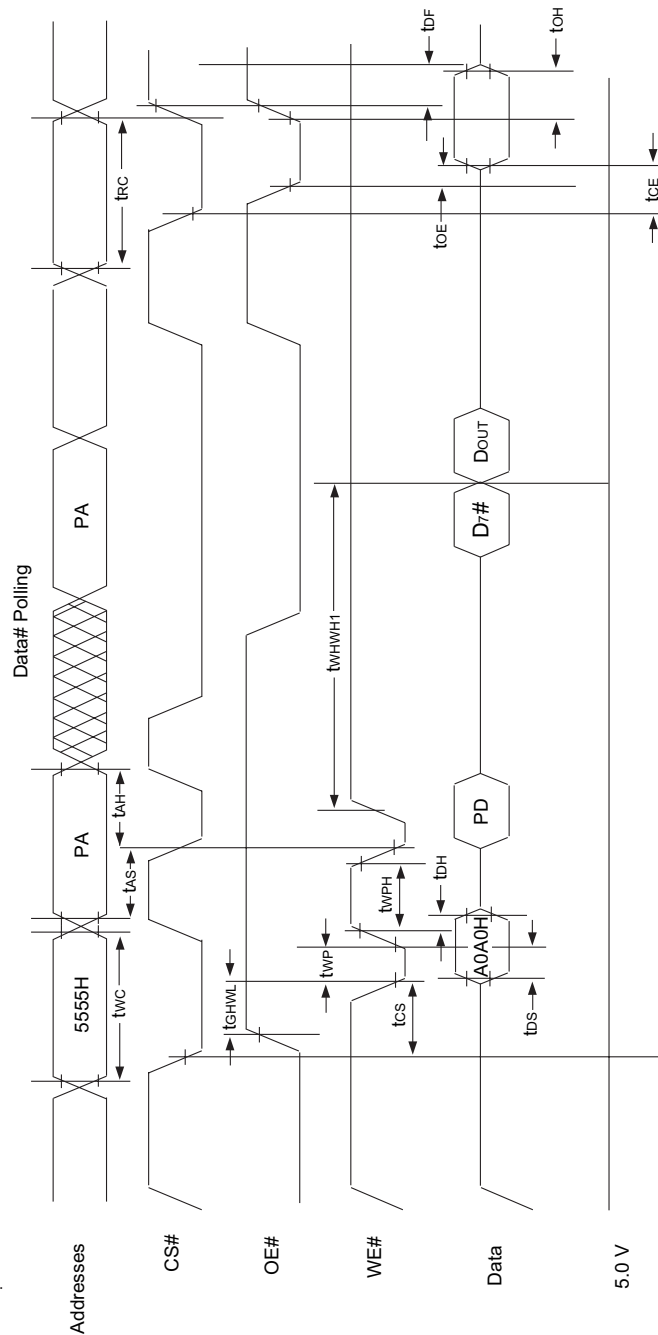


**AC WAVEFORMS FOR READ OPERATIONS**





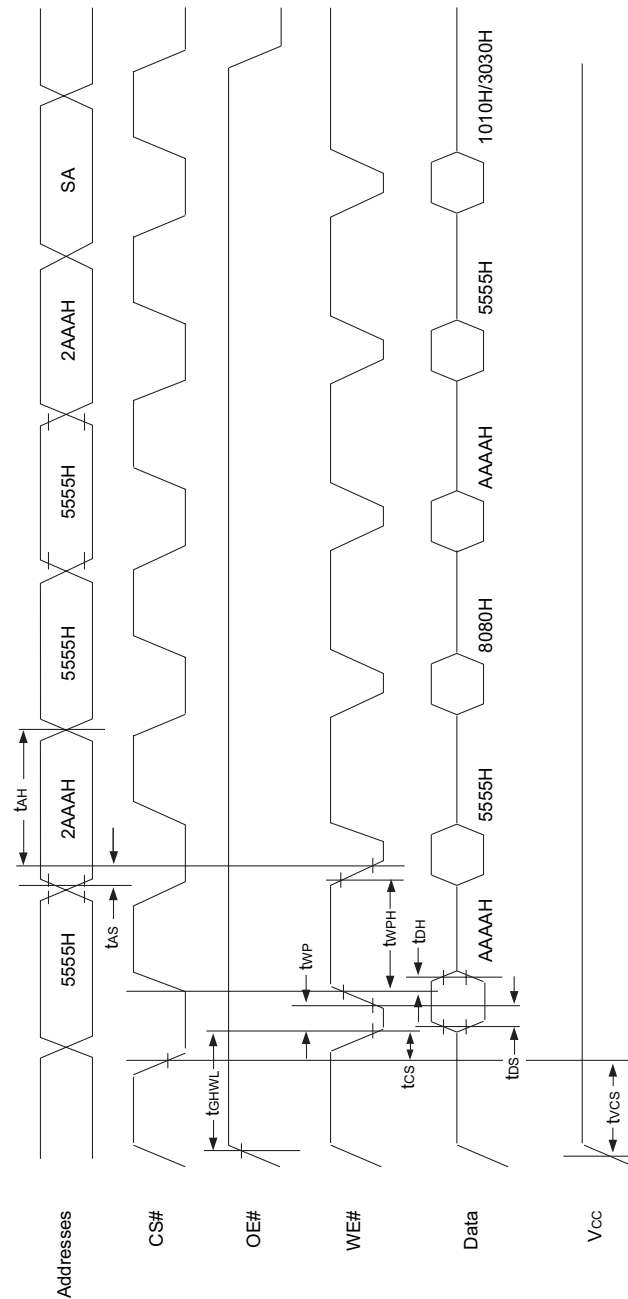
WRITE/ERASE/PROGRAM OPERATION, WE# CONTROLLED



- NOTES:
1. PA is the address of the memory location to be programmed.
  2. PD is the data to be programmed at byte address.
  3. D7# is the output of the complement of the data written to each chip.
  4. D<sub>OUT</sub> is the output of the data written to the device.
  5. Figure indicates last two bus cycles of four bus cycle sequence.



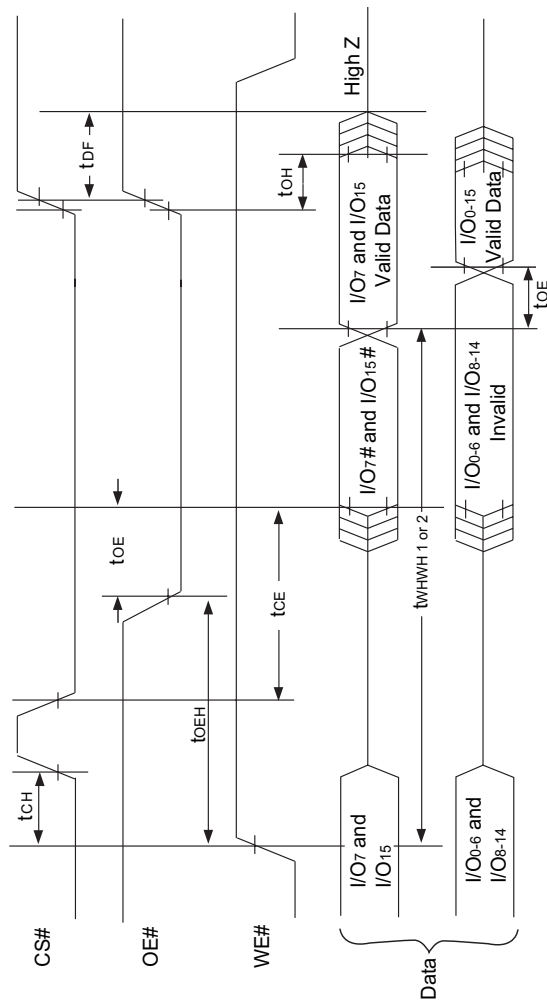
AC WAVEFORMS CHIP/SECTOR ERASE OPERATIONS



NOTE:  
1. SA is the sector address for Sector Erase.



AC WAVEFORMS FOR DATA# POLLING DURING EMBEDDED ALGORITHM OPERATIONS

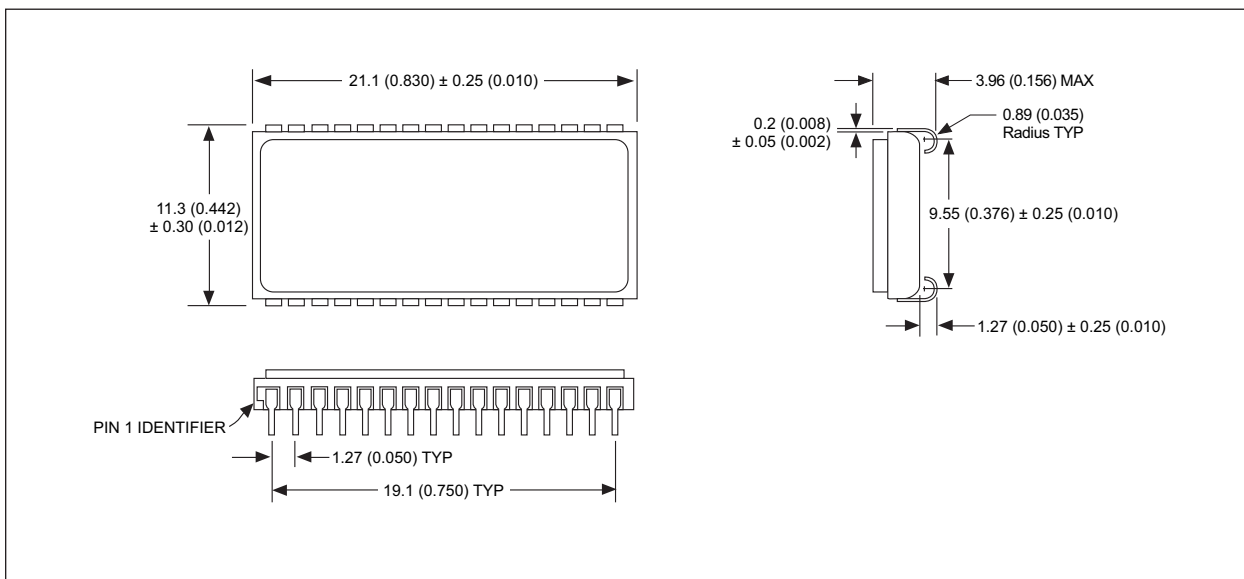






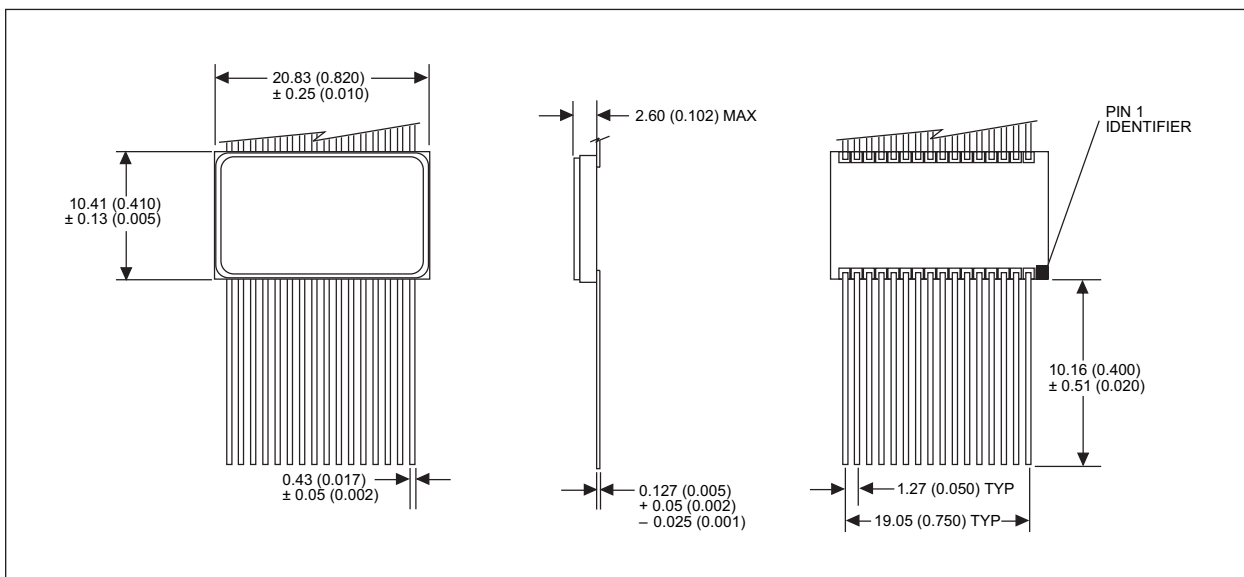


**PACKAGE 101: 32 LEAD, CERAMIC SOJ**



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES

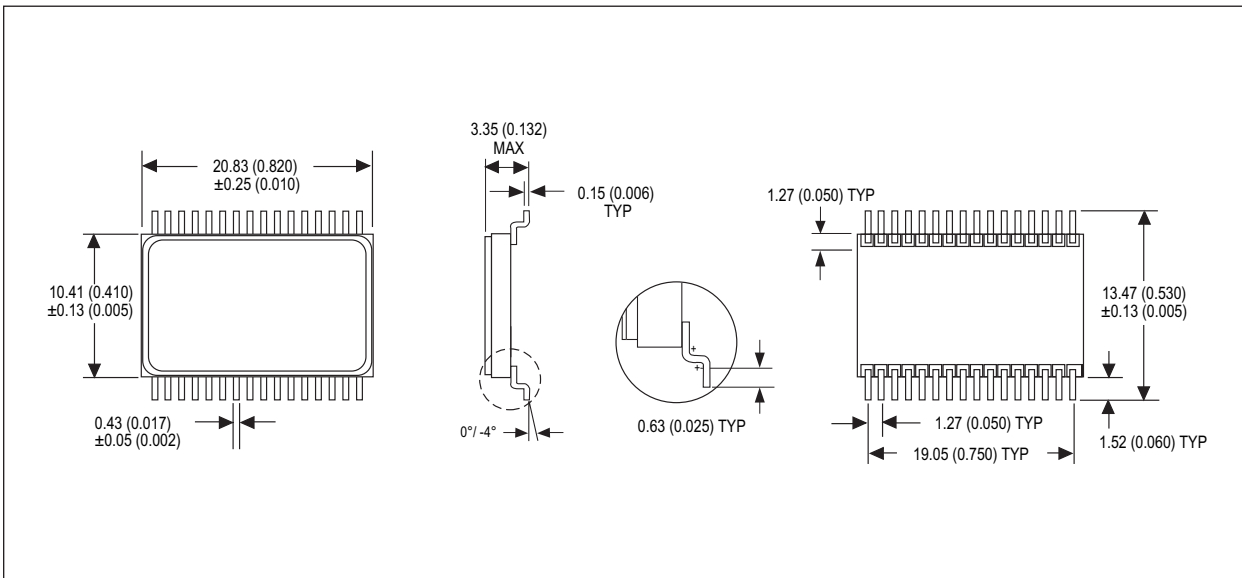
**PACKAGE 220: 32 LEAD, CERAMIC FLATPACK**



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES

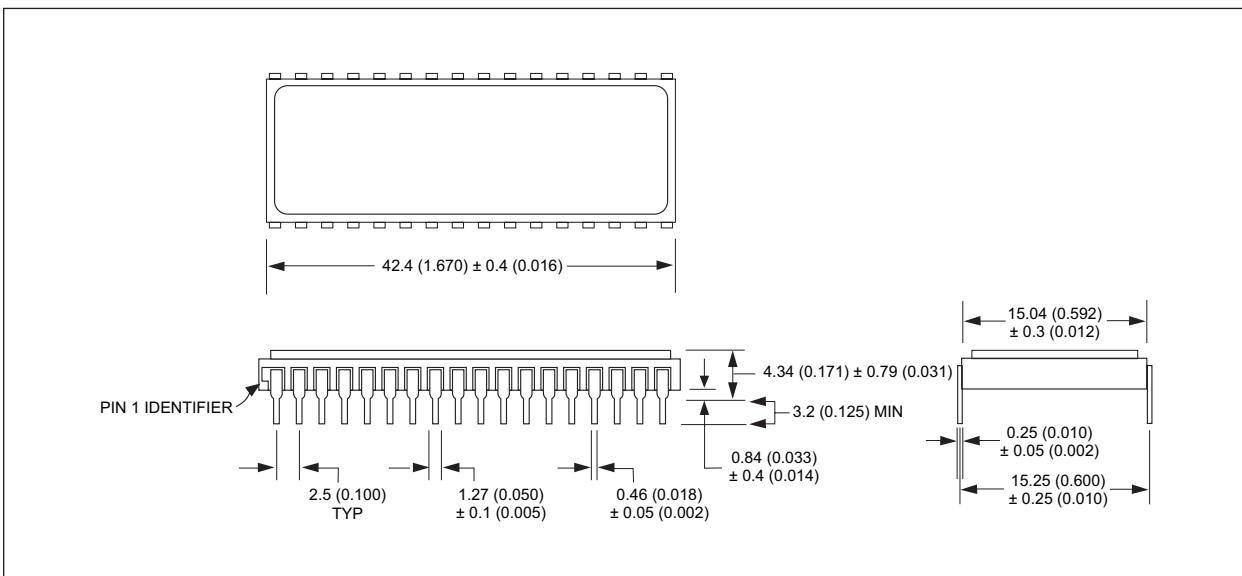


**PACKAGE 221: 32 LEAD, FORMED CERAMIC FLATPACK**



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES

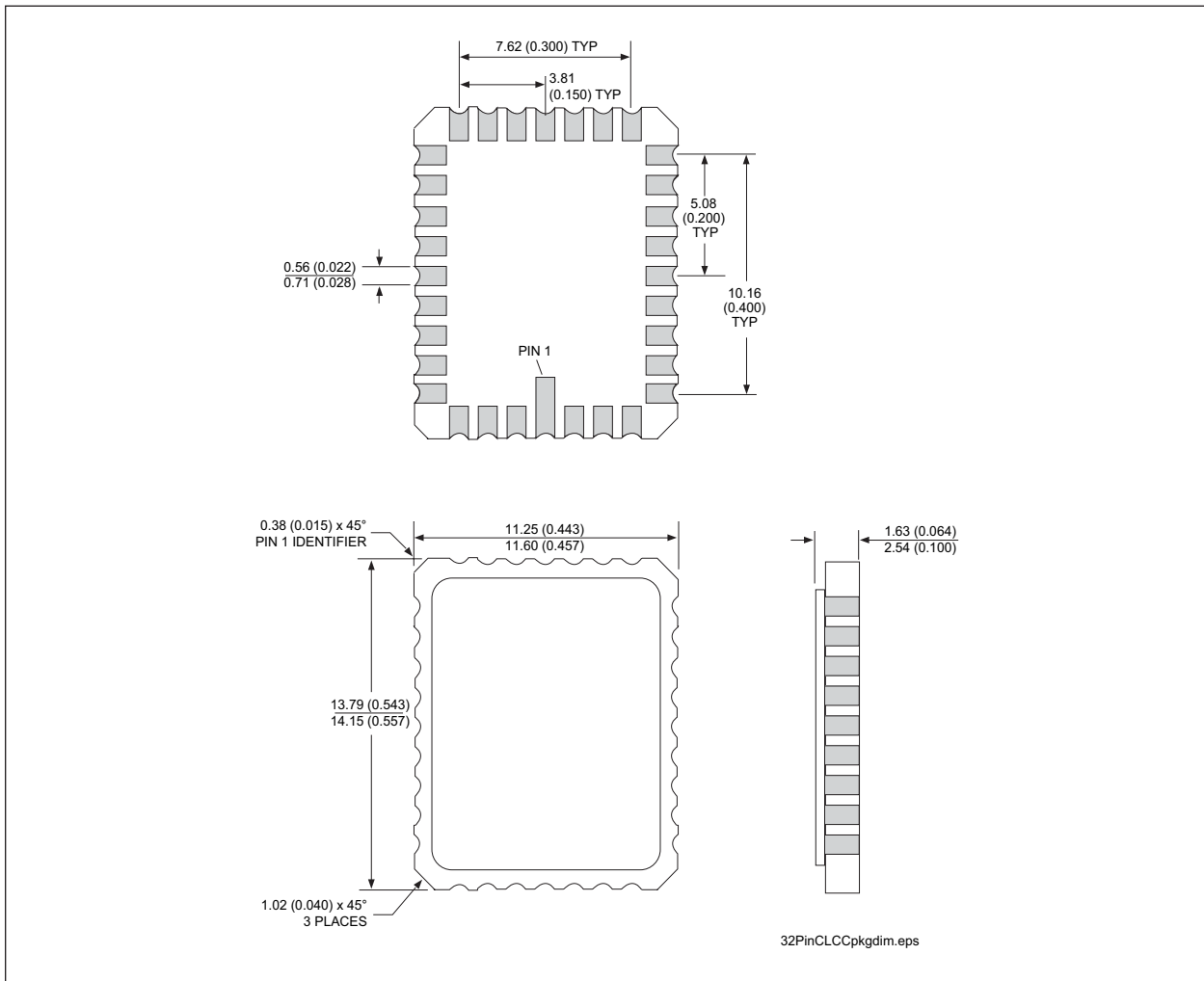
**PACKAGE 300: 32 PIN, CERAMIC DIP, SINGLE CAVITY SIDE BRAZED**



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES



**PACKAGE 601: 32 PIN, RECTANGULAR CERAMIC LEADLESS CHIP CARRIER**



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES



**ORDERING INFORMATION**

**W M F 128K8 -XXX X X 5 X**

**LEAD FINISH:**

Blank = Gold plated leads  
A = Solder dip leads

**V<sub>PP</sub> PROGRAMMING VOLTAGE**

5 = 5V

**DEVICE GRADE:**

Q = MIL-STD-883 Compliant  
M = Military Screened -55°C to +125°C  
I = Industrial -40°C to +85°C  
C = Commercial 0°C to +70°C

**PACKAGE TYPE:**

DE = 32 Lead Ceramic SOJ (Package 101)  
C = 32 Pin Ceramic DIP (Package 300)  
FE = 32 Lead Ceramic Flatpack (Package 220)  
FF = 32 Lead Formed Ceramic Flatpack (Package 221)  
CL = 32 Pin rectangular Ceramic Leadless Chip Carrier (Package 601)

**ACCESS TIME (ns)**

**ORGANIZATION, 128K x 8**

Flash

MONOLITHIC

WHITE ELECTRONIC DESIGNS CORP.



DEVICE TYPE	SECTOR SIZE	SPEED	PACKAGE	SMD NO.
128K x 8 Flash Monolithic	16KByte	150ns	32 pin DIP (C)	5962-96690 01HXX
128K x 8 Flash Monolithic	16KByte	120ns	32 pin DIP (C)	5962-96690 02HXX
128K x 8 Flash Monolithic	16KByte	90ns	32 pin DIP (C)	5962-96690 03HXX
128K x 8 Flash Monolithic	16KByte	70ns	32 pin DIP (C)	5962-96690 04HXX
128K x 8 Flash Monolithic	16KByte	60ns	32 pin DIP (C)	5962-96690 05HXX
128K x 8 Flash Monolithic	16KByte	150ns	32 lead SOJ (DE)	5962-96690 01HXX
128K x 8 Flash Monolithic	16KByte	120ns	32 lead SOJ (DE)	5962-96690 02HXX
128K x 8 Flash Monolithic	16KByte	90ns	32 lead SOJ (DE)	5962-96690 03HXX
128K x 8 Flash Monolithic	16KByte	70ns	32 lead SOJ (DE)	5962-96690 04HXX
128K x 8 Flash Monolithic	16KByte	60ns	32 lead SOJ (DE)	5962-96690 05HXX
128K x 8 Flash Monolithic	16KByte	150ns	32 lead Flatpack (FE)	5962-96690 01HTX
128K x 8 Flash Monolithic	16KByte	120ns	32 lead Flatpack (FE)	5962-96690 02HTX
128K x 8 Flash Monolithic	16KByte	90ns	32 lead Flatpack (FE)	5962-96690 03HTX
128K x 8 Flash Monolithic	16KByte	70ns	32 lead Flatpack (FE)	5962-96690 04HTX
128K x 8 Flash Monolithic	16KByte	60ns	32 lead Flatpack (FE)	5962-96690 05HTX
128K x 8 Flash Monolithic	16KByte	150ns	32 lead Formed Flatpack (FF)	5962-96690 01HUX
128K x 8 Flash Monolithic	16KByte	120ns	32 lead Formed Flatpack (FF)	5962-96690 02HUX
128K x 8 Flash Monolithic	16KByte	90ns	32 lead Formed Flatpack (FF)	5962-96690 03HUX
128K x 8 Flash Monolithic	16KByte	70ns	32 lead Formed Flatpack (FF)	5962-96690 04HUX
128K x 8 Flash Monolithic	16KByte	60ns	32 lead Formed Flatpack (FF)	5962-96690 05HUX